



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



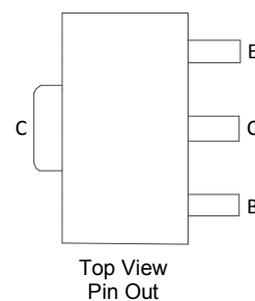
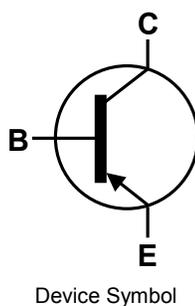
企业QQ二维码

## Features

- $BV_{CEO} = -200V$
- $I_C = -0.3A$  High Continuous Current
- Low Saturation Voltage  $V_{CE(sat)} < -200mV @ -0.1A$

## Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.05 grams (Approximate)



**Absolute Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-220	V
Collector-Emitter Voltage	$V_{CEO}$	-200	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Continuous Collector Current	$I_C$	-0.3	A
Peak Pulse Collector Current (single pulse)	$I_{CM}$	-1	A
Base Current	$I_B$	-200	A

**Thermal Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_D$	1	W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

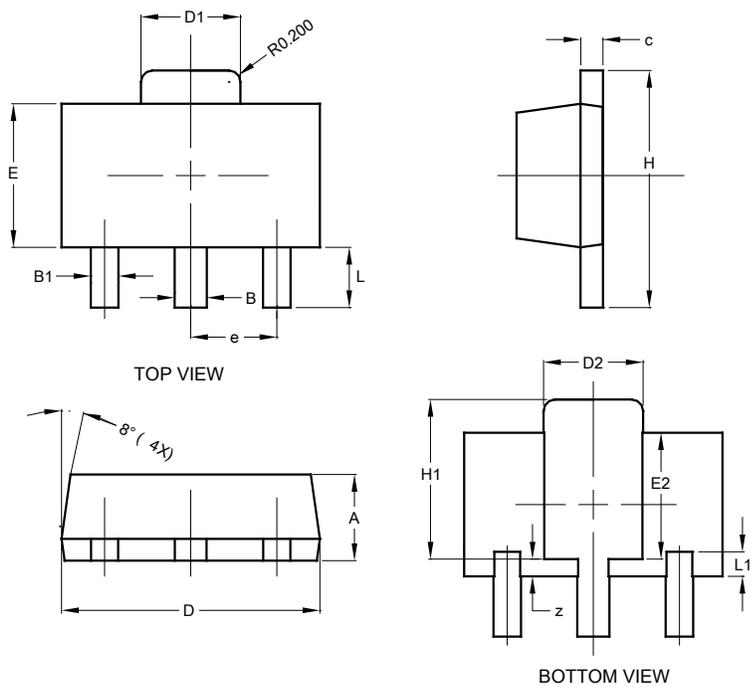
**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	-220	—	—	V	$I_C = -100\mu\text{A}$
Collector- Emitter Breakdown Voltage (Note 6)	$BV_{CEO}$	-200	—	—	V	$I_C = -10\text{mA}$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-5	—	—	V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$	—	—	-100	nA	$V_{CB} = -200\text{V}$
Emitter Cut-Off Current	$I_{EBO}$	—	—	-100	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	$I_{CES}$	—	—	-100	nA	$V_{CES} = -200\text{V}$
Collector-Emitter Saturation Voltage (Note 6)	$V_{CE(sat)}$	—	—	-0.2 -0.35	mV	$I_C = -100\text{mA}, I_B = -10\text{mA}$ $I_C = -250\text{mA}, I_B = -25\text{mA}$
Base-Emitter Saturation Voltage (Note 6)	$V_{BE(sat)}$	—	—	-1.0	mV	$I_C = -250\text{mA}, I_B = -25\text{mA}$
Base-Emitter Turn-On Voltage (Note 6)	$V_{BE(on)}$	—	—	-0.9	mV	$I_C = -250\text{mA}, V_{CE} = -10\text{V}$
DC Current Gain (Note 6)	$h_{FE}$	100 100 85 35	—	— — 300 —	—	$I_C = -1\text{mA}, V_{CE} = -10\text{V}$ $I_C = -100\text{mA}, V_{CE} = -10\text{V}$ $I_C = -250\text{mA}, V_{CE} = -10\text{V}$ $I_C = -400\text{mA}, V_{CE} = -10\text{V}$
Transitional frequency	$f_T$	150	—	—	MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	$C_{obo}$	—	—	10	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$

- Notes:
- For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device measured when operating in steady state condition.
  - Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

### Package Outline Dimensions

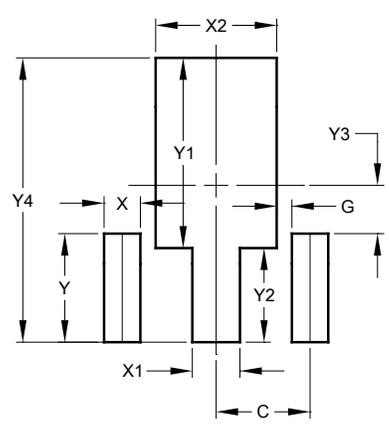
SOT89



SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

### Suggested Pad Layout

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530